

Jun Ho Son

List of Publications by Year in descending order

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30
papers

1,042
citations

430874

18
h-index

454955

30
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31
docs citations

31
times ranked

1598
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-Step LRET Aptasensor for Rapid Mycotoxin Detection. <i>Analytical Chemistry</i> , 2018, 90, 716-722.	6.5	49
2	Input-Specific Plasticity and Homeostasis at the <i>Drosophila</i> Larval Neuromuscular Junction. <i>Neuron</i> , 2017, 93, 1388-1404.e10.	8.1	118
3	Rapid Optical Cavity PCR. <i>Advanced Healthcare Materials</i> , 2016, 5, 167-174.	7.6	41
4	Ultrafast laser-assisted synthesis of hydrogenated molybdenum oxides for flexible organic solar cells. <i>Journal of Materials Chemistry A</i> , 2016, 4, 4755-4762.	10.3	38
5	The effect of localized surface plasmon resonance on the emission color change in organic light emitting diodes. <i>Nanoscale</i> , 2016, 8, 6463-6467.	5.6	19
6	Spontaneously Formed Nanopatterns on Polymer Films for Flexible Organic Light-Emitting Diodes. <i>Small</i> , 2015, 11, 4480-4484.	10.0	34
7	Ultrafast photonic PCR. <i>Light: Science and Applications</i> , 2015, 4, e280-e280.	16.6	176
8	Effect of reflective p-type ohmic contact on thermal reliability of vertical InGaN/GaN LEDs. <i>Electronic Materials Letters</i> , 2014, 10, 1171-1174.	2.2	4
9	Hemolysis-free blood plasma separation. <i>Lab on A Chip</i> , 2014, 14, 2287-2292.	6.0	74
10	MgO nano-facet embedded silver-based dielectric/metal/dielectric transparent electrode. <i>Optics Express</i> , 2012, 20, 845.	3.4	15
11	Enhancement of wall-plug efficiency in vertical InGaN/GaN LEDs by improved current spreading. <i>Optics Express</i> , 2012, 20, A287.	3.4	21
12	Modulation of surface plasmons coupling for enhancement of optical transmittance of silver-coated alkaline-earth metal films. <i>Journal of Materials Chemistry</i> , 2012, 22, 22859.	6.7	3
13	Design Rule of Nanostructures in Light-Emitting Diodes for Complete Elimination of Total Internal Reflection. <i>Advanced Materials</i> , 2012, 24, 2259-2262.	21.0	71
14	Enhancing Light Emission of Nanostructured Vertical Light-Emitting Diodes by Minimizing Total Internal Reflection. <i>Advanced Functional Materials</i> , 2012, 22, 632-639.	14.9	46
15	Design of Epitaxially Strained Ag Film for Durable Ag-Based Contact to p-Type GaN. <i>Crystal Growth and Design</i> , 2011, 11, 4943-4949.	3.0	10
16	Domain Matching Epitaxy of Mg-Containing Ag Contact on p-Type GaN. <i>Crystal Growth and Design</i> , 2011, 11, 2559-2563.	3.0	12
17	Effects of W diffusion barrier on inhibition of AlN formation in Ti/W/Al ohmic contacts on N-face n-GaN. <i>Applied Physics Letters</i> , 2011, 99, 233502.	3.3	6
18	Indium as an efficient ohmic contact to N-face n-GaN of GaN-based vertical light-emitting diodes. <i>Applied Physics Letters</i> , 2011, 99, 202106.	3.3	17

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19	Effects of Mg Additive on Inhibition of Ag Agglomeration in Ag-Based Ohmic Contacts on p-GaN. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H173.	2.2	22
20	Numerical analysis of efficiency droop induced by piezoelectric polarization in InGaN/GaN light-emitting diodes. <i>Applied Physics Letters</i> , 2010, 97, 032109.	3.3	25
21	Strain induced suppression of silver agglomeration of indium-containing silver contact. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	19
22	Strain engineering for the solution of efficiency droop in InGaN/GaN light-emitting diodes. <i>Optics Express</i> , 2010, 18, 5466.	3.4	76
23	MgO nano-pyramids structure for enhancement of light extraction efficiency in vertical light-emitting diodes. <i>Optics Express</i> , 2010, 18, A403.	3.4	9
24	Interfacial Band Bendings in Al Ohmic Contacts to Laser-Irradiated Ga-Face and N-Face n-GaN. <i>Electrochemical and Solid-State Letters</i> , 2009, 12, H405.	2.2	10
25	Effects of Ni cladding layers on suppression of Ag agglomeration in Ag-based Ohmic contacts on p-GaN. <i>Applied Physics Letters</i> , 2009, 95, 062108.	3.3	33
26	Highly reflective Ag-Cu alloy-based ohmic contact on p-type GaN using Ru overlayer. <i>Optics Letters</i> , 2008, 33, 2907.	3.3	14
27	Formation of High-Quality Ag-Based Ohmic Contacts to p-Type GaN. <i>Journal of the Electrochemical Society</i> , 2008, 155, H563.	2.9	21
28	Enhancement of light reflectance and thermal stability in Ag-Cu alloy contacts on p-type GaN. <i>Applied Physics Letters</i> , 2008, 93, 012102.	3.3	29
29	Highly reflective low resistance Ag-based Ohmic contacts on p-type GaN using Mg overlayer. <i>Applied Physics Letters</i> , 2007, 90, 012106.	3.3	19
30	Short range scattering effect of InAs quantum dots in the transport properties of two dimensional electron gas. <i>Applied Physics Letters</i> , 2007, 90, 152110.	3.3	11